



APT12067B2LLG Information



For Reference Only

Part Number APT12067B2LLG

Manufacturer Microsemi Corporation

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1200V 18A T-MAX

Package TO-247-3 Variant

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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APT12067B2LLG Specifications

Manufacturer Part Number APT12067B2LLG Manufacturer Microsemi Corporation Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Variant Series POWER MOS 7? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4420pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 565W (Tc) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant		
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SeriesPOWER MOS 7?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 2.5mAGate Charge (Qg) (Max) @ Vgs150nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4420pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)565W (Tc)Rds On (Max) @ Id, Vgs670 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4420pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 565W (Tc) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature 55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 7-MAX? [B2] Package / Case	Package	TO-247-3 Variant
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id SV @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4420pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature Supplier Device Package T-MAX? [B2] Package / Case 18A (Tc) 18B (Tc) 18B (Tc) 18A (Tc) 18A (Tc) 18V 18V 18V 10V 5V @ 2.5mA 4420pF @ 25V 4420pF @ 25V 4420pF @ 25V 4420pF @ 25V Though Hole	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4420pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Feth Feature Power Dissipation (Max) Feth Follow For Max	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4420pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 565W (Tc) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Current - Continuous Drain (Id) @ 25°C	18A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 4420pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 4420pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) S65W (Tc) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Vgs(th) (Max) @ Id	5V @ 2.5mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)565W (Tc)Rds On (Max) @ Id, Vgs670 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	Gate Charge (Qg) (Max) @ Vgs	150nC @ 10V
FET Feature - Power Dissipation (Max) 565W (Tc) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Input Capacitance (Ciss) (Max) @ Vds	4420pF @ 25V
Power Dissipation (Max) 565W (Tc) Rds On (Max) @ Id, Vgs 670 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs670 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Power Dissipation (Max)	565W (Tc)
Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Rds On (Max) @ Id, Vgs	670 mOhm @ 9A, 10V
Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3 Variant	Mounting Type	Through Hole
	Supplier Device Package	T-MAX? [B2]
Report errors?	Package / Case	TO-247-3 Variant
		Report errors?

APT12067B2LLG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

APT12067B2LLG Payment Methods



















APT12067B2LLG Shipping Methods













If you have any question about APT12067B2LLG, please do not hesitate to contact us!

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